

Silicon NPN Power Transistor

KSD5090

DESCRIPTION

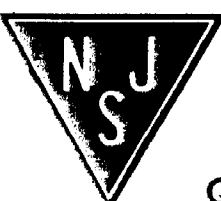
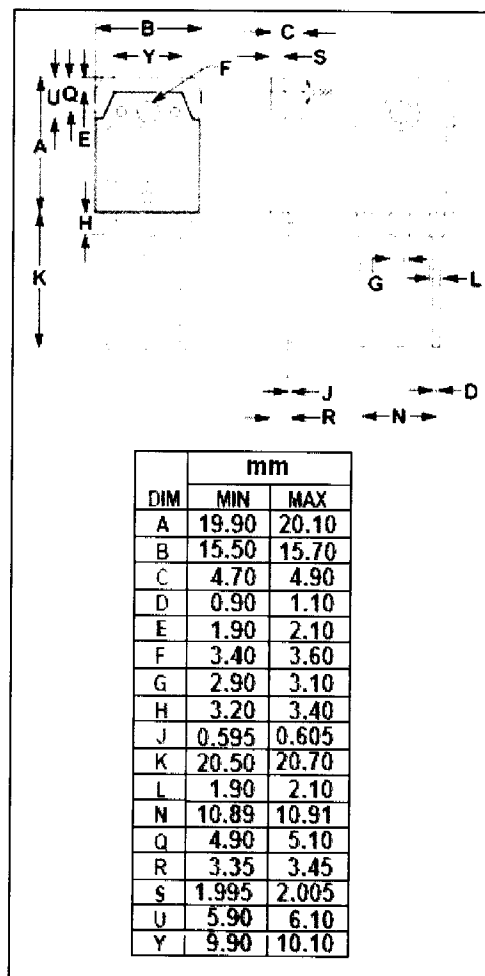
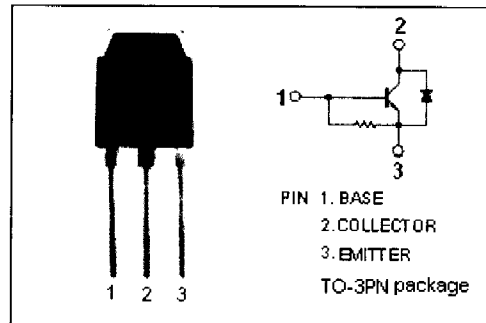
- High Breakdown Voltage-
 : $V_{CBO} = 1500V$ (Min)
- High Switching Speed
- High Reliability
- Built-in Damper Diode

APPLICATIONS

- Designed for color TV horizontal output applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current- Continuous	8	A
I_{CP}	Collector Current-Peak	30	A
P_C	Collector Power Dissipation @ $T_c=25^\circ C$	150	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



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ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=6A; I_B=1.2A$			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=6A; I_B=1.2A$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=800V; I_E=0$			10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=4V; I_C=0$	40		200	mA
h_{FE-1}	DC Current Gain	$I_C=1A; V_{CE}=5V$	8			
h_{FE-2}	DC Current Gain	$I_C=6A; V_{CE}=5V$	5			
V_{ECF}	C-E Diode Forward Voltage	$I_F=8A$			2.0	V
t_f	Fall Time	$I_C=6A, I_{B1}=1.2A; I_{B2}=-2.4A$ $R_L=33.3\Omega; V_{CC}=200V$			0.3	μs